L Number	Hits	Search Text	DB	Time stamp
1	10575	mixed adj2 oxide	USPAT;	2002/10/05 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	7645	doped adj2 oxide	USPAT;	2002/10/05 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/40/05 45:40
15	13425	doped near3 oxide	USPAT;	2002/10/05 15:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	40500	(1) A b word downing at money? (conide that only 20) and the contract that	IBM_TDB	2002/10/05 15:20
22	16563	(dopant doped doping) near3 (oxide "Al.sub.2" adj "O.sub.3")	USPAT;	2002/10/05 15:20
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	50000	() and the desire and the desire and the desired and the desi	IBM_TDB	2002/40/05 45:42
29	53032	(dopant doped doping mixed) near5 (oxide "Al.sub.2" adj	USPAT;	2002/10/05 15:43
		"O.sub.3")	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	404405	(IBM_TDB	2002/10/05 16:02
36	184465	(substrate deposit\$3 sputter\$4 cosputter\$4) near12	USPAT;	2002/10/05 16.02
		("25.degree." "25" ((ambient room) adj (temperature temp))	US-PGPUB;	
		"20.degree." "20")	EPO; JPO;	
			DERWENT;	
40	0544	(/-:::	IBM_TDB	2002/10/05 15:24
43	3514	((silicon adj monoxide) or SiO) near15 (sputter\$4 evaporat\$3	USPAT;	2002/10/05 15.24
		cosputter\$4 coevaporat\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
· ·	0460	((/ A out 2 odi O out 2) or Al2O2 or alumina or camphira	IBM_TDB USPAT;	2002/10/05 15:44
50	9169	((("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or sapphire) with (source target)) or ((aluminum adj oxide) with (source	US-PGPUB;	2002/10/03 13.44
			EPO; JPO;	
		target))	DERWENT;	
			IBM TDB	
E 7	12	(//cilican adi manavida) or SiO) near15 (sputter\$1	USPAT;	2002/10/05 15:34
57	12	(((silicon adj monoxide) or SiO) near15 (sputter\$4 evaporat\$3 cosputter\$4 coevaporat\$3)) same (((("Al.sub.2"	US-PGPUB;	2002/10/00 10:04
		adj "O.sub.3") or Al2O3 or alumina or sapphire) with (source	EPO; JPO;	
1		target)) or ((aluminum adj oxide) with (source target)))	DERWENT;	
		targetij or ((alaminam aaj oxide) with (source targetij))	IBM_TDB	
64	12349	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj	USPAT;	2002/10/05 15:42
~~	12573	((dopant doped doping mixed) flears (oxide Al.3db.2 adj	US-PGPUB;	
		S. Sab. S // Saints (Simboli St Ol)	EPO; JPO;	
			DERWENT:	
			IBM TDB	
71	37	(((silicon adj monoxide) or SiO) near15 (sputter\$4	USPAT;	2002/10/05 15:35
	57	evaporat\$3 cosputter\$4 coevaporat\$3)) and (((dopant doped	US-PGPUB:	
		doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) same	EPO; JPO;	
		(silicon or Si))	DERWENT;	
16		\(\sigma_{ij}\)	IBM_TDB	
78	8632	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj	USPAT;	2002/10/05 15:43
	3002	"O.sub.3")) near15 (silicon or Si)	US-PGPUB;	
1		() () () () () () () () () ()	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

				1 0000/40/05 45 40
85	2534	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (((dopant doped doping mixed) near5	USPAT; US-PGPUB; EPO; JPO;	2002/10/05 15:43
		(oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si))	DERWENT; IBM TDB	
99	7572	(Si silicon) near5 (dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")	USPAT; US-PGPUB;	2002/10/05 15:44
			EPO; JPO; DERWENT;	
106	1554	(Si or silicon) near10 (dopant doped doping mixed) near10	IBM_TDB USPAT;	2002/10/05 15:46
		(("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide))	US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	
113	176	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp))	USPAT; US-PGPUB;	2002/10/05 15:46
		"20.degree." "20")) and ((Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or	EPO; JPO; DERWENT;	
120	8	alumina or (aluminum adj oxide))) ((substrate deposit\$3 sputter\$4 cosputter\$4) near12	IBM_TDB USPAT;	2002/10/05 15:46
		("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) same ((Si or silicon) near10 (dopant	US-PGPUB; EPO; JPO;	
		doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide)))	DERWENT; IBM_TDB	0000/40/05 45:47
92	328	((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp))	USPAT; US-PGPUB;	2002/10/05 15:47
		"20.degree." "20")) same (((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) near15 (silicon or Si))	EPO; JPO; DERWENT; IBM_TDB	
127	20636	(substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp))	USPAT; US-PGPUB;	2002/10/05 16:01
		"20.degree.")	EPO; JPO; DERWENT;	
141	0	((Si or silicon) near10 (dopant doped doping mixed) near10	IBM_TDB USPAT;	2002/10/05 15:48
•••		(("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum adj oxide))) same ((substrate deposit\$3 sputter\$4	US-PGPUB; EPO; JPO;	
		cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))	DERWENT; IBM_TDB	
134	41	((Si or silicon) near10 (dopant doped doping mixed) near10 (("Al.sub.2" adj "O.sub.3") or Al2O3 or alumina or (aluminum	USPAT; US-PGPUB;	2002/10/05 15:48
		adj oxide))) and ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature	EPO; JPO; DERWENT;	
148	1	temp)) "20.degree.")) ((substrate deposit\$3 sputter\$4 cosputter\$4) near12	IBM_TDB USPAT;	2002/10/05 15:56
		("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 (thermal adj budget)	US-PGPUB; EPO; JPO;	
	F90	(cool\$4 near3 (substrate wafer)) near20 ((substrate deposit\$3	DERWENT; IBM_TDB USPAT;	2002/10/05 16:01
155	589	sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree."))	US-PGPUB; EPO; JPO;	2002/10/05 10:01
		adj (temperature temp)) 20.degree.))	DERWENT; IBM TDB	
162	34	((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) and ((cool\$4 near3 (substrate wafer)) near20	USPAT; US-PGPUB;	2002/10/05 15:57
		((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp))	EPO; JPO; DERWENT;	
		"20.degree.")))	IBM_TDB	2002/10/05 16:03
169	3	((cool\$4 near3 (substrate wafer)) near20 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree."	USPAT; US-PGPUB;	2002/10/05 16:03
		((ambient room) adj (temperature temp)) "20.degree."))) and	EPO; JPO;	
		(applied adj materials).asn.	DERWENT; IBM TDB	

((ambient room) adj (temperature temp)) "20.degree." "20") ((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (applied adj materials).asn. ((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "20")) and (applied adj materials).asn. ((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; "25" ((ambient room) adj (temperature temp)) "20.degree." US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	176	70836	(deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25"	USPAT;	2002/10/05 16:07
183	176	/0030	((ambient room) adi (temperature temp)) "20 degree " "20")	1	2002/10/00 10:0/
183		1	(tambient room) adjitemperature temp); 20.degree. 20)		
183				1	
183					
("(ambient room) adj (temperature temp)) "20.degree." "20")) and (applied adj materials).asn. ("((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT, IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB;	183	717	(/_deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." "25"		2002/10/05 16:05
and (applied adj materials).asn. EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USP	100			-	
190 76 ((((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT					
190 76 (((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO;			(4) (4) (4) (4) (4) (4) (4) (4) (4) (4)		
"25" ((ambient room) adj (temperature temp)) "20.degree." "20")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) 197				IBM TDB	
197 107 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ((substrate deposit\$3 sputter\$4) near12 ((substrate deposit\$3 sputter\$4] near12 ((su	190	76	(((deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree."	USPAT;	2002/10/05 16:05
197 107 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 (US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; US-				US-PGPUB;	
197			"20")) and (applied adj materials).asn.) and ((dopant doped	EPO; JPO;	
107 ((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp))			doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3"))	DERWENT;	
("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) and (applied adj materials).asn. 18 (((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) 211 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.") 218 56 ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 2002/10/05 16:0				IBM_TDB	
18	197	107		USPAT;	2002/10/05 16:05
18 (((substrate deposit\$3 sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) ("20.degree.")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) DERWENT; BPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; USPAT; US-PGPUB; US-PGPU				,	
18			"20.degree.")) and (applied adj materials).asn.	, ,	
18				The state of the s	
("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.") 218 56 ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; room) adj (temperature temp)) "20.degree." ((ambient room) adj (temperature temp)) "20.degree.")				-	
"20.degree.")) and (applied adj materials).asn.) and ((dopant doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.") 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; room) adj (temperature temp)) "20.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20	204	18			2002/10/05 16:05
doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3")) 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.") 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; IBM_TDB USPAT; IBM_TDB USPAT; IBM_TDB USPAT; ISPAT; ISP					
211 1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) uspAT; us-pgpuB; EPO; JPO; DERWENT; IBM_TDB uspAT; uspective ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) uspAT; uspective ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) uspAT; uspAT; uspAT; uspAT; uspective ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) uspAT; uspAT; uspective (uspatient) uspAT; uspatient (uspatient) uspAT; us					
1224 (sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USP			doped doping mixed) near5 (oxide "Al.sub.2" adj "O.sub.3"))	1	
adj (temperature temp)) "20.degree.") US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; VS-PGPUB; US-PGPUB; US-PGPUB; US-PGPUB;			10 100 11 11 11 11 11 11 11 11 11 11 11		0000/40/05 40:07
EPO; JPO; DERWENT; IBM_TDB ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; US-PGPUB;	211	1224			2002/10/05 16:07
DERWENT; IBM_TDB USPAT; voom) adj (temperature temp)) "20.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 US-PGPUB;			adj (temperature temp)) "20.degree.")	1	
218 56 ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient room) adj (temperature temp)) "20.degree.")) near20 IBM_TDB USPAT; US-PGPUB;					
218 56 ((sputter\$4 cosputter\$4) near12 ("25.degree." ((ambient usPAT; room) adj (temperature temp)) "20.degree.")) near20 us-PGPUB;					
room) adj (temperature temp)) "20.degree.")) near20 US-PGPUB;	040	50	//anuttared accountared) near12 ("25 degree" //ambient		2002/10/05 16:00
	218	56			2002/10/03 10:09
thecessary conventional conventionally typical essential temporary, and, if					
beneficial beneficially typically) DERWENT;					
IBM TDB			beneficial beneficially typically)		